

BYC20X-600

Rectifier diode, hyperfast

Rev. 01 — 29 November 2007

Product data sheet

1. Product profile

1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features

- Extremely fast switching
- Low reverse recovery current
- Reduces switching loss in associated MOSFET
- Low thermal resistance
- Isolated package

1.3 Applications

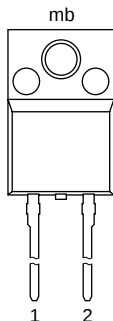
- Half-bridge or full-bridge switched-mode power supplies
- Half-bridge lighting ballasts
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

1.4 Quick reference data

- $V_{RRM} \leq 600$ V
- $V_F = 1.54$ V (typ)
- $I_{F(AV)} \leq 20$ A
- $t_{rr} = 19$ ns (typ)

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode (k)		 001aaa020
2	anode (a)		
mb	mounting base; isolated		

SOD113 (2-lead TO-220F)

3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BYC20X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; $\delta = 1.0$; $T_h \leq 100\text{ }^{\circ}\text{C}$	-	500	V
$I_{F(AV)}$	average forward current	square waveform; $\delta = 0.5$; $T_h \leq 25\text{ }^{\circ}\text{C}$	-	20	A
I_{FRM}	repetitive peak forward current	square waveform; $\delta = 0.5$; $T_h \leq 25\text{ }^{\circ}\text{C}$; $t_p = 25\text{ }\mu\text{s}$	-	40	A
I_{FSM}	non-repetitive peak forward current	$t = 10\text{ ms}$; sinusoidal waveform	-	250	A
		$t = 8.3\text{ ms}$; sinusoidal waveform	-	274	A
T_{stg}	storage temperature		-40	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 1	-	-	2.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

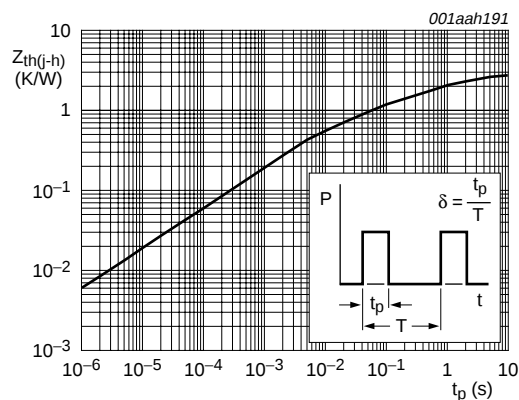


Fig 1. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

$T_h = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

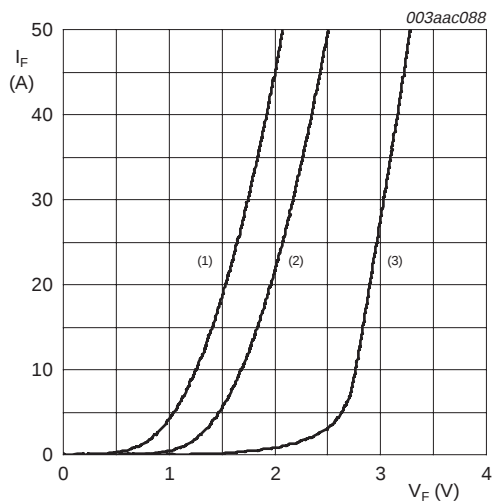
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; $f = 50\text{ Hz to }60\text{ Hz}$; sinusoidal waveform; relative humidity $\leq 65\%$; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	from pin 1 (cathode) to external heatsink; $f = 1\text{ MHz}$	-	10	-	pF

7. Characteristics

Table 6. Characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _F	forward voltage	I _F = 20 A; T _j = 150 °C; see Figure 2	-	1.54	1.97	V
		I _F = 40 A; T _j = 150 °C; see Figure 2	-	1.95	2.34	V
		I _F = 20 A; see Figure 2	-	1.89	2.9	V
I _R	reverse current	V _R = 600 V	-	16	200	μA
		V _R = 500 V; T _j = 100 °C	-	1.6	3.0	mA
Dynamic characteristics						
t _{rr}	reverse recovery time	I _F = 1 A to V _R = 30 V; dI _F /dt = 50 A/μs; see Figure 3	-	35	55	ns
		I _F = 20 A to V _R = 400 V; dI _F /dt = 500 A/μs; see Figure 3				
		T _j = 25 °C	-	19	-	ns
		T _j = 100 °C	-	32	40	ns
I _{RM}	peak reverse recovery current	I _F = 20 A to V _R = 400 V; T _j = 125 °C; see Figure 3				
		dI _F /dt = 50 A/μs	-	3.0	7.5	A
		dI _F /dt = 500 A/μs	-	9.5	12	A
V _{FR}	forward recovery voltage	I _F = 20 A; dI _F /dt = 100 A/μs; see Figure 4	-	8	11	V



- (1) $T_j = 150\text{ }^{\circ}\text{C}$; typical values
- (2) $T_j = 150\text{ }^{\circ}\text{C}$; maximum values
- (3) $T_j = 25\text{ }^{\circ}\text{C}$; maximum values

Fig 2. Forward current as a function of forward voltage

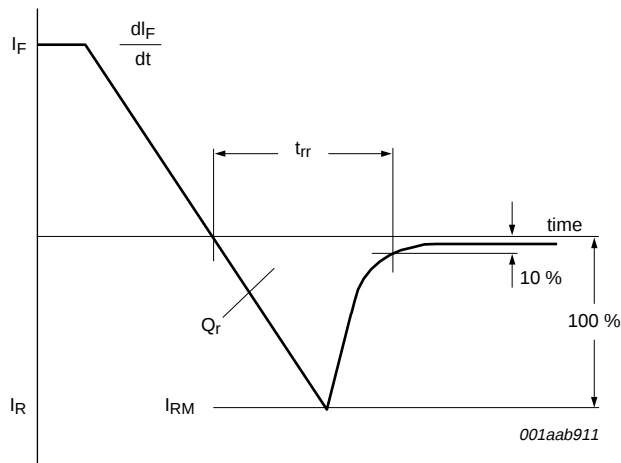


Fig 3. Reverse recovery definitions

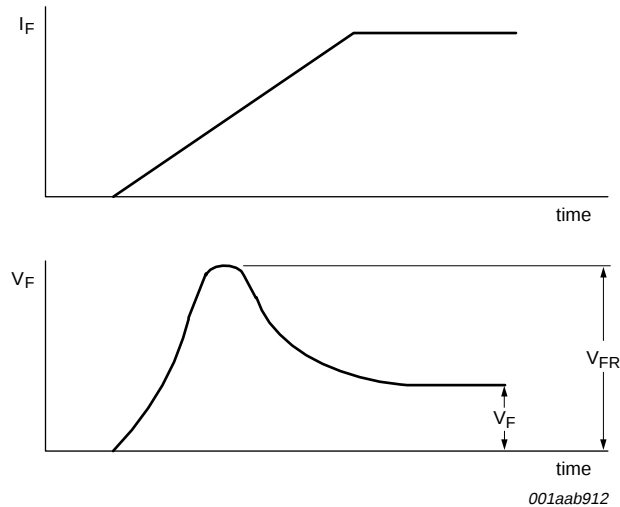
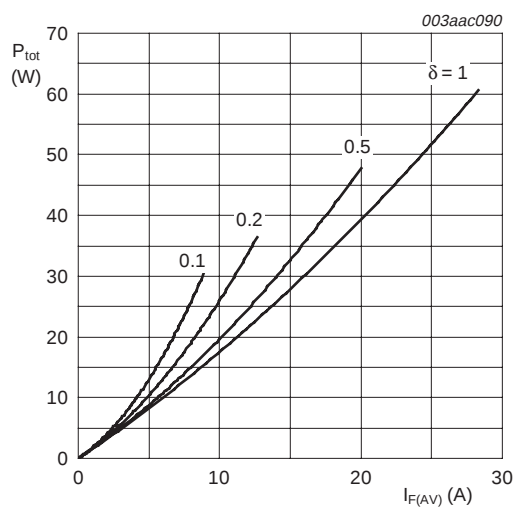
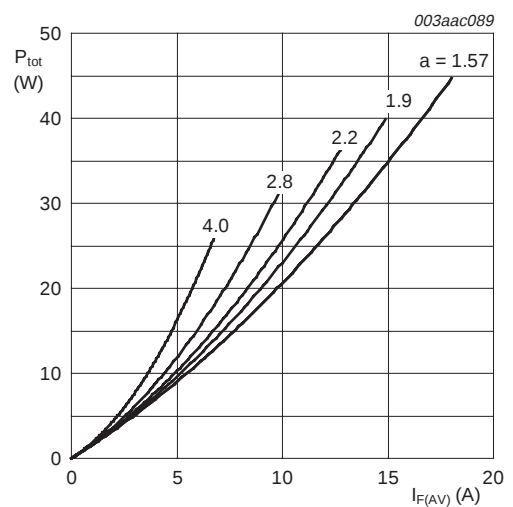


Fig 4. Forward recovery definitions



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 2-lead TO-220 'full pack'

SOD113

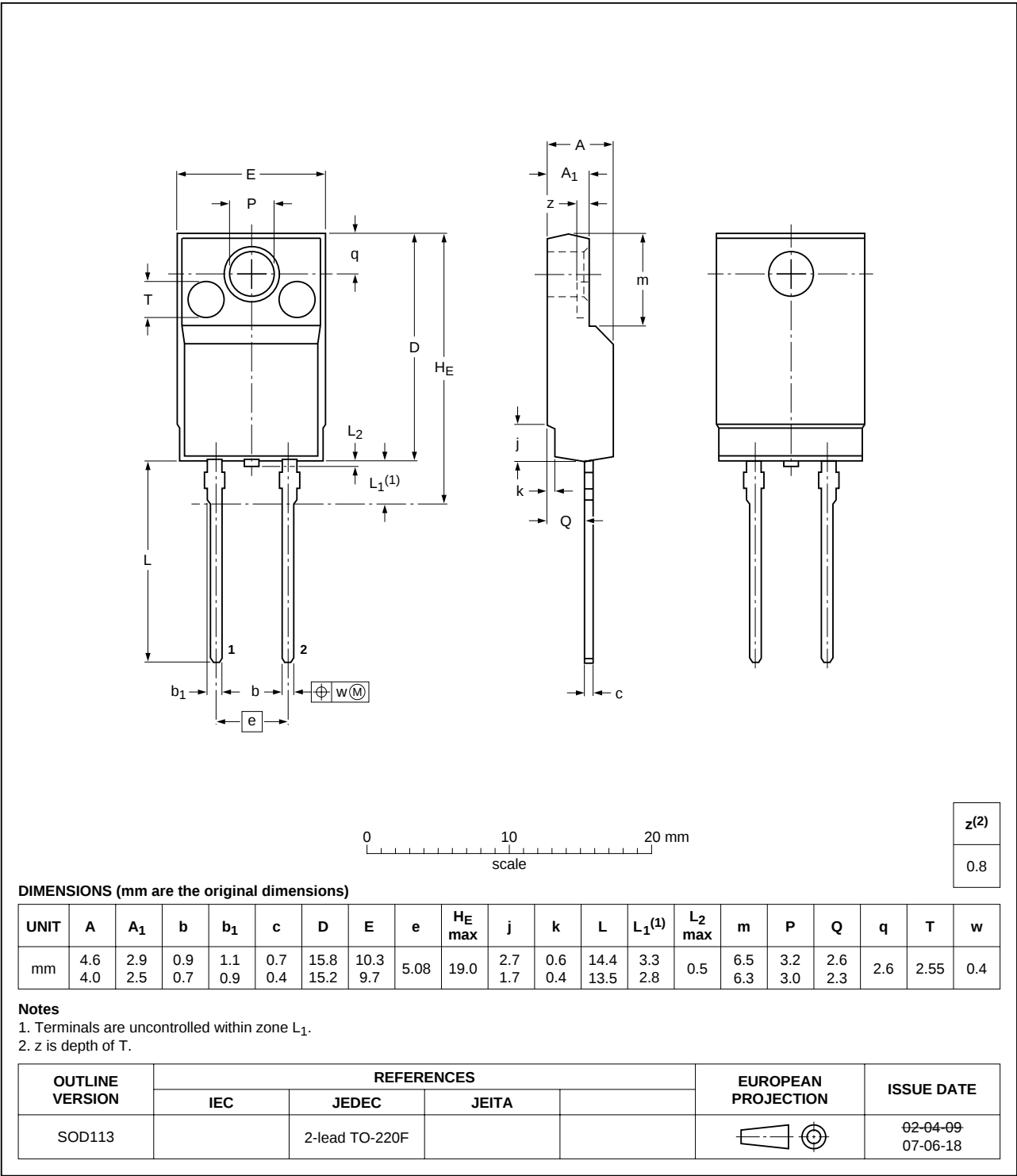


Fig 7. Package outline SOD113 (2-lead TO-220F)

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC20X-600_1	20071129	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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